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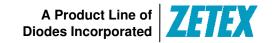












100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = 25°C
100V	350mΩ @ VGS = 10V	3.5A
	450mΩ @ VGS = 6V	3.1A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- DC-DC Converters
- Power management functions
- Uninterrupted power supply

Features and Benefits

- Fast switching speed
- Low input capacitance
- "Green" Component and RoHS compliant (Note 1)
- · Qualified to AEC-Q101 Standards for High Reliability

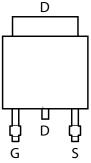
Mechanical Data

- Case: TO252-3L
- Case Material: Molded Plastic "Green" Molding Compound, UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)

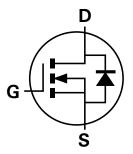




Top View



Pin Out - Top View



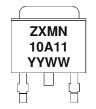
Equivalent Circuit

Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A11KTC	See Below	13	16	2,500

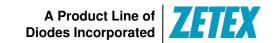
Note: 1. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

Marking Information



ZXMN = Product Type Marking Code, Line 1 10A11 = Product Type Marking Code, Line 2 YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01-52)





Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	100	V
Gate-Source voltage			V _{GS}	±20	V
Continuous Drain current	V _{GS} = 10V	(Note 3) T _A = 70°C (Note 3) (Note 2)	ID	3.5 2.8 2.4	A
Pulsed Drain current V _{GS} = 10V (Note 4		(Note 4)	I _{DM}	9.9	Α
Continuous Source current (Body diode) (Note 3)		(Note 3)	Is	8.4	A
Pulsed Source current (Body diode) (Note 4)		I _{SM}	9.9	Α	

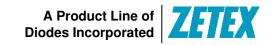
Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
	(Note 2)		4.06 32.4	
Power dissipation Linear derating factor	(Note 3)	P _D	8.5 68.0	W mW/°C
	(Note 6)		2.11 16.8	
	(Note 2)		30.8	
Thermal Resistance, Junction to Ambient	(Note 3)	$R_{\theta JA}$	14.7	°C/W
	(Note 6)	, and the second	59.1	
Thermal Resistance, Junction to Lead	(Note 5)	$R_{ heta JL}$	1.10	°C/W
Operating and storage temperature range		T _J , T _{STG}	-55 to 150	°C

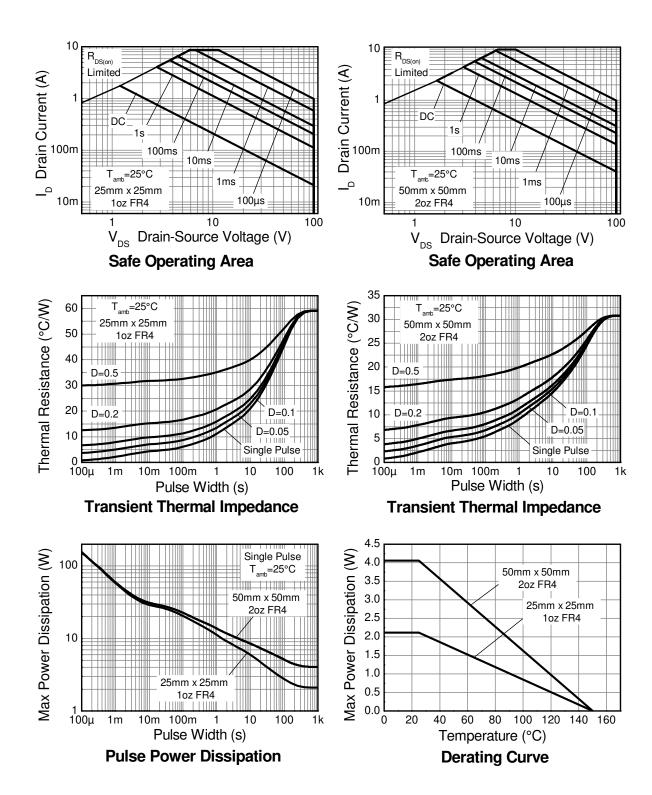
Notes:

- 2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 3. Same as note 2, except the device is measured at $t \le 10$ sec.
- 4. Same as note 2, except the device is pulsed with D = 0.02 and pulse width 300 μs. The pulse current is limited by the maximum junction temperature. 5. Thermal resistance from junction to solder-point (at the end of the drain lead).
- 6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with the high coverage single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

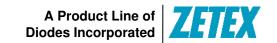




Thermal Characteristics







Electrical Characteristics @TA = 25°C unless otherwise specified

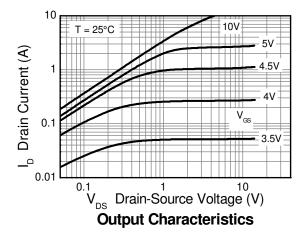
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV_{DSS}	100	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(th)}$	2	_	4	V	$I_D = 250 \mu A$, $V_{DS} = V_{GS}$	
Static Drain Source On Decistones (Note 7)	J			0.350	Ω	$V_{GS} = 10V, I_D = 2.6A$	
Static Drain-Source On-Resistance (Note 7)	R _{DS (ON)}		_	0.450	12	$V_{GS} = 6V, I_D = 1.3A$	
Forward Transconductance (Notes 7 & 8)	9 _{fs}	_	4	_	S	V _{DS} = 15V, I _D = 2.6A	
Diode Forward Voltage (Note 7)	V_{SD}	_	0.850	0.950	V	I _S = 1.85A, V _{GS} = 0V	
Reverse recovery time (Note 8)	t _{rr}	_	26	_	ns		
Reverse recovery charge (Note 8)	Q_{rr}	_	30	_	nC	$I_S = 1.0A$, di/dt = 100A/ μ s	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	274	_	рF	V 50V V 0V	
Output Capacitance	Coss	_	21	_	рF	V _{DS} = 50V, V _{GS} = 0V - f = 1MHz	
Reverse Transfer Capacitance	Crss	_	11	_	рF	71 = 1101112	
Total Gate Charge (Note 9)	Q_g	_	3.5	_	nC	$V_{GS} = 6V$	
Total Gate Charge (Note 9)	Qq	_	5.4	_	nC	$V_{DS} = 50V$,	
Gate-Source Charge (Note 9)	Q_{gs}	_	1.4	_	nC	$V_{GS} = 10V$ $I_{D} = 2.5A$	
Gate-Drain Charge (Note 9)	Q_{gd}	_	1.5	_	nC	7	
Turn-On Delay Time (Note 9)	t _{D(on)}	_	2.7	_	ns		
Turn-On Rise Time (Note 9)	t _r	_	1.7	_	ns	$V_{DD} = 50V, V_{GS} = 10V$	
Turn-Off Delay Time (Note 9)	t _{D(off)}	_	7.4	_	ns	$I_D = 1.0A, R_G \cong 6\Omega$	
Turn-Off Fall Time (Note 9)	t _f	_	3.5	_	ns]	

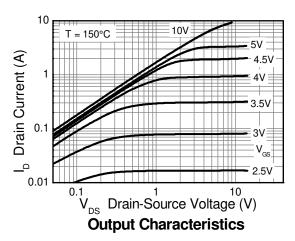
Notes:

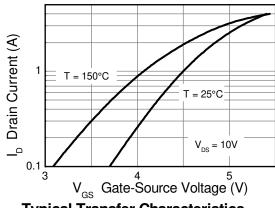
- 7. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$
- 8. For design aid only, not subject to production testing.
 9. Switching characteristics are independent of operating junction temperatures.

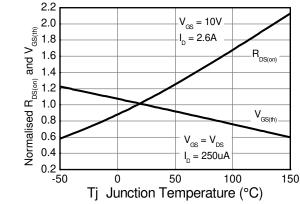


Typical Characteristics



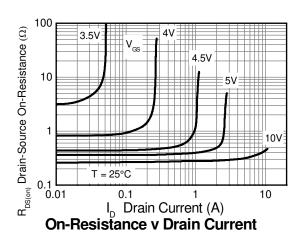


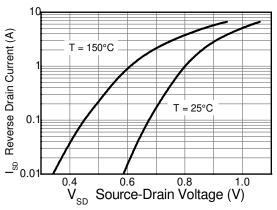




Typical Transfer Characteristics

Normalised Curves v Temperature

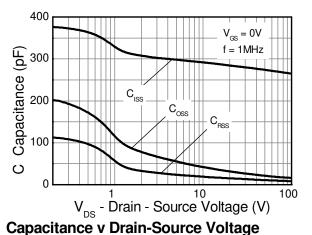


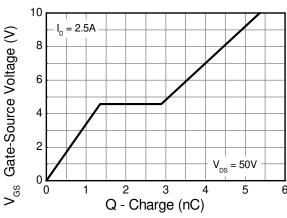


Source-Drain Diode Forward Voltage



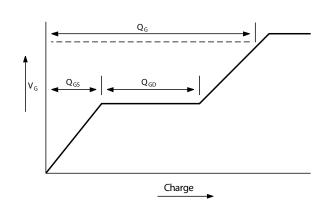
Typical Characteristics - continued





Gate-Source Voltage v Gate Charge

Test Circuits

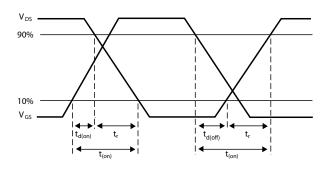


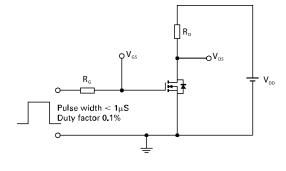
Jacob Jacob

Current regulator

Basic gate charge waveform

Gate charge test circuit

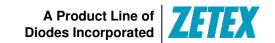




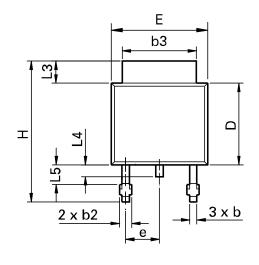
Switching time waveforms

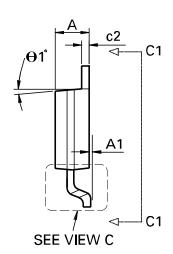
Switching time test circuit

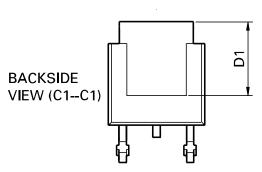


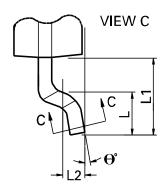


Package Outline Dimensions



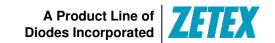




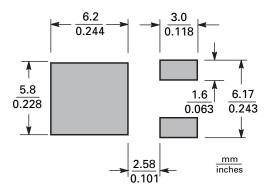


DIM Inches		hes	Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	0.086	0.094	2.18	2.39	е	0.090 BSC		2.29 BSC	
A 1	-	0.005	-	0.127	Н	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
С	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-





Suggested Pad Layout



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